AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended): A process for producing a microswitch, ~~characterized in that it comprises~~ comprising at least the following steps:

[[•]] ~~production~~ producing [[of]] a first subassembly [[(100)]] ~~comprising~~ having a first substrate [[(8)]] and at least conducting lines ~~(2, 3, 10 and 11)~~ and a control electrode [[(5)]];

[[•]] ~~production~~ producing [[of]] a second subassembly [[(101)]] ~~comprising~~ having a second substrate [[(21)]], at least one stop layer [[(18)]], a layer of material [[(15)]], at least one electrically conducting layer ~~(16, 17)~~ and at least one high-permittivity layer [[(7)]];

[[•]] assembling the two subassemblies mechanical and electrical ~~assembly of the two subassemblies (100, 101)~~;

[[•]] ~~elimination of~~ eliminating the second substrate [[(21)]] down to the stop layer [[(18)]]; and

[[•]] final cutting of the layer [[(17)]] to the dimensions of a membrane [[(1)]] by photolithography and etching.

2. (currently amended): The process for producing a microswitch as claimed in claim 1, ~~characterized in that~~ wherein the high-permittivity layer is deposited by a sputtering or sol-gel process.

3. (currently amended): The process for producing a microswitch as claimed in claim 1, ~~characterized in that~~ wherein the substrate [[(8)]] has regions of additional thickness, called mesas [[(81)]], and a conducting layer [[(19)]], each mesa being covered with a thickness [[(14)]] of metal identical to that of the conducting lines ~~(2, 3, 10 and 11)~~.

4. (currently amended): The process for producing a microswitch as claimed in claim 3, ~~characterized in that~~ wherein the conducting layer ~~(16, 17)~~ has, facing the mesas [[(81)]], regions [[(12)]] of additional thickness that are produced in the same material as the layer [[(7)]] and have the same thickness.

5. (currently amended): The process for producing a microswitch as claimed in claim 3, ~~characterized in that~~ wherein, for a parallel-type microswitch comprising, on the first subassembly [[(100)]], two conducting lines ~~(10, 11)~~ located on the insulating substrate [[(8)]], which are mutually parallel and electrically connected to an electrical ground; a conducting line [[(2)]], called the input signal line which is placed between the ground lines ~~(10, 11)~~ and is parallel to said ground lines; a conducting line [[(3)]] called the output signal line which is placed in the extension of the input signal line [[(2)]] and between the ground lines ~~(10, 11)~~, which is parallel to said ground lines and a control electrode [[(5)]] located on said substrate, one of the ends of which electrically connects the input signal line [[(2)]] and the output signal line [[(3)]], and the two subassemblies ~~(100, 101)~~ are joined together by the deposition and bonding of a eutectic alloy [[(19)]] between the ground lines ~~(10, 11)~~ and the conducting layers ~~(16, 17)~~, the regions [[(12)]] of additional thickness resting on the mesas [[(81)]].

6. (currently amended): The process for producing a microswitch as claimed in claim 5, ~~characterized in that~~ wherein the eutectic alloy is of the gold/tin type.

7. (currently amended): The process for producing a microswitch as claimed in claim 1, ~~characterized in that~~ wherein at least one deposition of deformable metal [[(20)]] is carried out on the first subassembly [[(100)]].

8. (currently amended): The process for producing a microswitch as claimed in claim 7, ~~characterized in that~~ wherein the deformable material is either gold or a gold/tin eutectic alloy.

9. (currently amended): The process for producing a microswitch as claimed in claim 7, ~~characterized in that~~ wherein the production of the second subassembly [[(101)]] comprises the following substeps:

[[•]] ~~production~~ producing [[of]] an assembly ~~comprising~~ having the first substrate [[(21)]], at least the stop layer [[(18)]] and the layer of material [[(15)]];

[[•]] cutting of the layer [[(15)]] so as to create at least one pillar [[(13)]]; and

[[•]] deposition of the electrically conducting layer [[(16, 17)]] and at least the layer [[(7)]] on the layer [[(15)]].

10. (currently amended): The process for producing a microswitch as claimed in claim 7, ~~characterized in that~~ wherein the second subassembly [[(101)]] is joined to the first subassembly [[(100)]] by anodic bonding at its pillar or pillars [[(13)]].

11. (currently amended): The process for producing a microswitch as claimed in ~~one of~~ claim[[s]] 7 ~~to 10~~, ~~characterized in that~~, wherein in the case of a parallel-type switch, the electrical connection between the ground lines ~~(10, 11)~~ and the conducting layers ~~(16, 17)~~ is produced by means of the deposit or deposits of metal [[(20)]].

12. (currently amended): The process for producing a plurality of microswitches as claimed in claim [[[25]]] 1, ~~characterized in that~~ wherein a plurality of subassemblies [[(100)]] are produced on a common substrate [[(8)]] and a plurality of subassemblies [[(101)]] are produced on a common substrate [[(21)]], the joining operation being common to the two subassemblies ~~(100, 101)~~, the whole assembly obtained then being cut in order to obtain a plurality of individual microswitches.

13. (new): The process for producing a microswitch as claimed in claim 8, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

14. (new): The process for producing a microswitch as claimed in claim 9, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.

15. (new): The process for producing a microswitch as claimed in claim 10, wherein in the case of a parallel-type switch, the electrical connection between the ground lines and the conducting layers is produced by means of the deposit or deposits of metal.